

Listing of the Claim:

This listing of the claims will replace all prior versions, and listings, of claims in the application. Please cancel, without prejudice, claims 42-50.

Listing of the Claim:

(Claims 1-36 have been cancelled)

37.(Previously Presented) A method of improving data retention in a nonvolatile writeable memory having an erased-cell reference level and a programmed-cell reference level, the nonvolatile writeable memory having a plurality of memory cells, each of the memory cells being in an erased state when storing a charge below the erased-cell reference level, and each of the memory cells being in a programmed state when storing a charge above the programmed-cell reference level, the method comprising the steps of:

(a) identifying a memory cell having a charge above the erased-cell reference level and below the programmed-cell reference level; and

(b) programming the memory cell until the charge of the memory cell is above the programmed-cell reference level.

(Claim 38 has been cancelled)

39.(Previously Presented) A method of improving data retention within a nonvolatile writeable memory, the method comprising the steps of:

(a) identifying a group of one or more memory cells having a stored charge over a first threshold and less than a second threshold; and

(b) programming each memory cell of the group of one or more cells until each of the memory cells has a stored charge over the second threshold.

40.(Previously Presented) The method of claim 39 wherein the first threshold corresponds to an erased-cell reference level plus a guardband level.

41.(Previously Presented) The method of claim 37 wherein the identifying corresponds to identifying a memory cell having a charge above the erased-cell reference level plus a guardband level.

(Claims 42-50 have been cancelled)